

isc Silicon NPN Power Transistor

DESCRIPTION

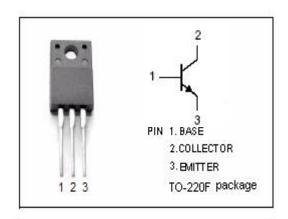
- · Collector-Emitter Breakdown Voltage-
- : V_{(BR)CEO}= 50V(Min)
- · Low Collector Saturation Voltage-
 - : V_{CE(sat)}= 0.4V(Max.)
- · Wide Area of Safe Operation
- Complement to Type 2SB1136
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

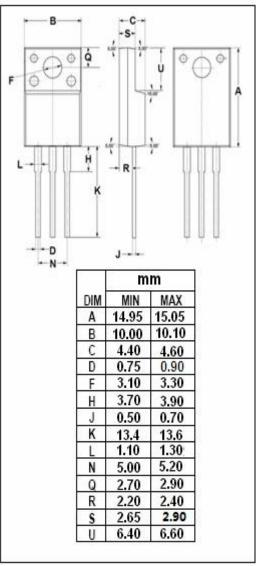


• Designed for relay drivers, high speed inverters, converters and other general high current switching applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{СВО}	Collector-Base Voltage	60	V	
Vceo	Collector-Emitter Voltage	50	V	
V _{EBO}	Emitter-Base Voltage	6	V	
Ic	Collector Current-Continuous	12	А	
I _{CM}	Collector Current-Peak	15	А	
P _C	Collector Power Dissipation @T _a =25℃	2	W	
	Collector Power Dissipation @T _C =25°C	30		
TJ	Junction Temperature 150		$^{\circ}$	
T _{stg}	Storage Temperature	-55~150	$^{\circ}$	







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2SD1669

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1 mA; R _{BE} = ∞	50			٧
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	60			٧
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	6			٧
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 0.6A			0.4	V
Ісво	Collector Cutoff Current	V _{CB} = 40V ; I _E = 0			100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			100	μ A
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 2V	70		280	
h _{FE-2}	DC Current Gain	I _C = 5A; V _{CE} = 2V	30			
f⊤	Current-Gain—Bandwidth Product	I _C = 1A; V _{CE} = 5V		10		MHz
Switching Times						
ton	Turn-On Time			0.1		μ \$
t _{stg}	Storage Time	$I_C = 2A$, $I_{B1} = I_{B2} = 0.2A$; $R_L = 4 \Omega$; $V_{CC} = 20V$		1.2		μ \$
t _f	Fall Time			0.05		μS

♦ h_{FE-1} Classifications

Q	R	S
70-140	100-200	140-280

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